

RADIATION HARDENED PNP POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/545

DEVICES

2N5151	2N5153
2N5151L	2N5153L
2N5151U3	2N5153U3

LEVELS

JANSM – 3K Rads (Si)
JANSD – 10K Rads (Si)
JANSP – 30K Rads (Si)
JANSL – 50K Rads (Si)
JANSR – 100K Rads (Si)
JANSF – 300K Rads (Si)

ABSOLUTE MAXIMUM RATINGS ($T_C = +25^\circ\text{C}$ unless otherwise noted)

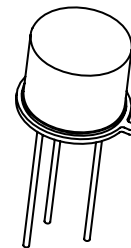
Parameters / Test Conditions	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	80	Vdc
Collector-Base Voltage	V_{CBO}	100	Vdc
Emitter-Base Voltage	V_{EBO}	5.5	Vdc
Collector Current	I_C	2.0	Adc
Total Power Dissipation 2N5151, 2N5153, L @ $T_A = +25^\circ\text{C}$ (1) 2N5151, 2N5153, L @ $T_C = +25^\circ\text{C}$ (2) 2N5151U3, 2N5153U3 @ $T_A = +25^\circ\text{C}$ (3) 2N5151U3, 2N5153U3 @ $T_C = +25^\circ\text{C}$ (4)	P_T	1.0 10 1.16 100	W
Operating & Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	$^\circ\text{C}$
Thermal Resistance, Junction-to Case	$R_{\theta JC}$	10 1.75 (U3)	$^\circ\text{C/W}$

Note:

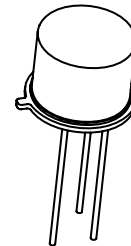
- 1) Derate linearly 5.7mW/ $^\circ\text{C}$ for $T_A > +25^\circ$
- 2) Derate linearly 66.7mW/ $^\circ\text{C}$ for $T_A > +25^\circ$
- 3) Derate linearly 6.63mW/ $^\circ\text{C}$ for $T_A > +25^\circ$
- 4) Derate linearly 571mW/ $^\circ\text{C}$ for $T_A > +25^\circ$

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted)

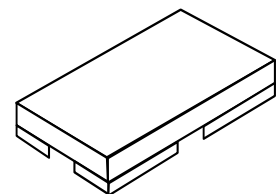
Parameters / Test Conditions	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage $I_C = 100\text{mAdc}, I_B = 0$	$V_{(BR)CEO}$	80		Vdc
Emitter-Base Cutoff Current $V_{EB} = 4.0\text{Vdc}, I_C = 0$ $V_{EB} = 5.5\text{Vdc}, I_C = 0$	I_{EBO}		1.0 1.0	μAdc mAdc
Collector-Emitter Cutoff Current $V_{CE} = 60\text{Vdc}, V_{BE} = 0$ $V_{CE} = 100\text{Vdc}, V_{BE} = 0$	I_{CES}		1.0 1.0	μAdc mAdc
Collector-Base Cutoff Current $V_{CE} = 40\text{Vdc}, I_B = 0$	I_{CEO}		50	μAdc



TO-5
2N5151L, 2N5153L
 (See Figure 1)



TO-39 (TO-205AD)
2N5151, 2N5153



U-3
2N5151U3, 2N5153U3

RADIATION HARDENED PNP POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/545

ELECTRICAL CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS				
Forward-Current Transfer Ratio $I_C = 50\text{mA}$, $V_{CE} = 5\text{Vdc}$		20		
2N5151		50		
2N5153				
$I_C = 2.5\text{A}$, $V_{CE} = 5\text{Vdc}$	h_{FE}	30	90	
2N5151		70	200	
2N5153				
$I_C = 5\text{A}$, $V_{CE} = 5\text{Vdc}$		20		
2N5151		40		
2N5153				
Collector-Emitter Saturation Voltage $I_C = 2.5\text{A}$, $I_B = 250\text{mA}$ $I_C = 5.0\text{A}$, $I_B = 500\text{mA}$	$V_{CE(sat)}$		0.75 1.5	Vdc
Base-Emitter Voltage Non-Saturation $I_C = 2.5\text{A}$, $V_{CE} = 5\text{Vdc}$	V_{BE}		1.45	Vdc
Base-Emitter Saturation Voltage $I_C = 2.5\text{A}$, $I_B = 250\text{mA}$ $I_C = 5.0\text{A}$, $I_B = 500\text{mA}$	$V_{BE(sat)}$		1.45 2.2	Vdc

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 500\text{mA}$, $V_{CE} = 5\text{Vdc}$, $f = 10\text{MHz}$				
2N5151	$ h_{fe} $	6		
2N5153		7		
Common-Emitter Small-Signal Short-Circuit Forward-Current Transfer Ratio $I_C = 100\text{mA}$, $V_{CE} = 5\text{Vdc}$, $f = 1\text{kHz}$				
2N5151	h_{fe}	20		
2N5153		50		
Output Capacitance $V_{CB} = 10\text{Vdc}$, $I_E = 0$, $f = 1.0\text{MHz}$	C_{obo}		250	pF

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Turn-On Time $I_C = 5\text{A}$, $I_{B1} = 500\text{mA}$ $I_{B2} = -500\text{mA}$ $R_L = 6\Omega$ $V_{BE(OFF)} = 3.7\text{Vdc}$	t_{on}		0.5	μs
Turn-Off Time $I_C = 5\text{A}$, $I_{B1} = 500\text{mA}$ $I_{B2} = -500\text{mA}$ $R_L = 6\Omega$ $V_{BE(OFF)} = 3.7\text{Vdc}$	t_{off}		1.5	μs

6 Lake Street, Lawrence, MA 01841
 1-800-446-1158 / (978) 620-2600 / Fax: (978) 689-0803
 Website: <http://www.microsemi.com>

RADIATION HARDENED PNP POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/545

SWITCHING CHARACTERISTICS (cont.)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Storage Time $I_C = 5\text{Adc}$, $I_{B1} = 500\text{mAdc}$ $I_{B2} = -500\text{mAdc}$	t_s		1.4	μs
Fall Time $R_L = 6\Omega$ $V_{BE(OFF)} = 3.7\text{Vdc}$	t_f		0.5	μs

SAFE OPERATING AREA

DC Tests

$T_C = +25^\circ\text{C}$, 1 Cycle, $t_p = 1.0\text{s}$

Test 1

$V_{CE} = 5.0\text{Vdc}$, $I_C = 2.0\text{Adc}$

Test 2

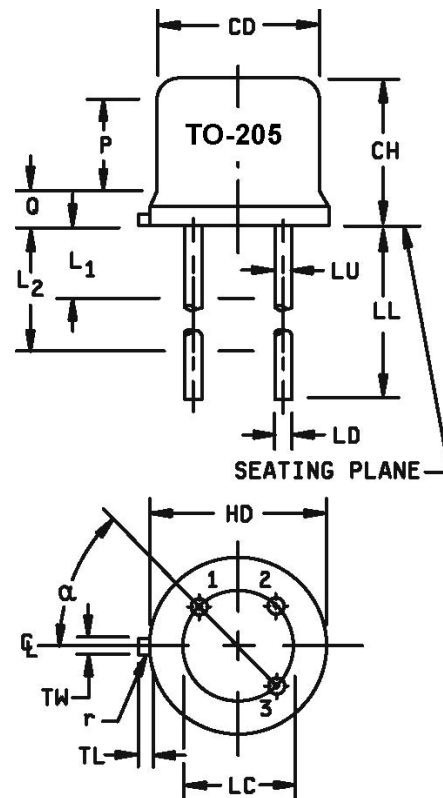
$V_{CE} = 32\text{Vdc}$, $I_C = 310\text{mAdc}$

Test 3

$V_{CE} = 80\text{Vdc}$, $I_C = 14.5\text{mAdc}$

**FIGURE 1 (TO-5, TO-39)
 PACKAGE DIMENSIONS**

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	6
CH	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200 TP		5.08 TP		7
LD	.016	.021	0.41	0.53	8, 9
LL	See notes 8, 9, 12, 13				
LU	.016	.019	0.41	0.48	8, 9
L1		.050		1.27	8, 9
L2	.250		6.35		8, 9
Q		.050		1.27	6
TL	.029	.045	0.74	1.14	4, 5
TW	.028	.034	0.71	0.86	3
r		.010		0.25	11
α	45° TP		45° TP		7
P	.100		2.54		



RADIATION HARDENED PNP POWER SILICON TRANSISTOR

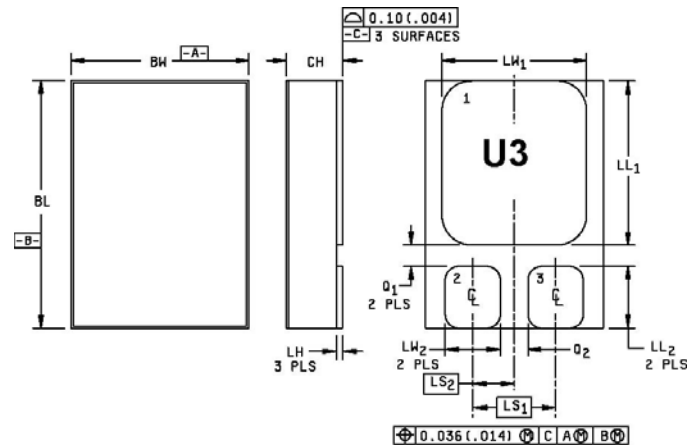
Qualified per MIL-PRF-19500/545

NOTES:

- 1 Dimensions are in inches.
- 2 Millimeters are given for general information only.
- 3 Beyond r (radius) maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
- 4 TL measured from maximum HD.
- 5 Outline in this zone is not controlled.
- 6 CD shall not vary more than .010 inch (0.25 mm) in zone P. This zone is controlled for automatic handling.
- 7 Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
- 8 LU applied between L1 and L2. LD applies between L2 and LL minimum. Diameter is uncontrolled in L1 and beyond LL minimum.
- 9 All three leads.
- 10 The collector shall be electrically and mechanically connected to the case.
- 11 r (radius) applies to both inside corners of tab.
- 12 In accordance with ASME Y14.5M, diameters are equivalent to ϕx symbology.
- 13 For transistor types 2N5151 and 2N5153, LL is .5 inch (13 mm) minimum, and .75 inch (19 mm) maximum.
- 14 For transistor types 2N5151L and 2N5153L, LL is 1.5 inch (38 mm) minimum and 1.75 inch (44.4 mm) maximum.
- 15 Lead designation, depending on device type, shall be as follows: lead numbering; lead 1 = emitter, lead 2 = base, and lead 3 = collector.

FIGURE 2 (U3)
 PACKAGE DIMENSIONS

Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.395	.405	10.04	10.28
BW	.291	.301	7.40	7.64
CH	.1085	.1205	2.76	3.06
LH	.010	.020	0.25	0.51
LL1	.220	.230	5.59	5.84
LL2	.115	.125	2.93	3.17
LS1	.150 BSC		3.81 BSC	
LS2	.075 BSC		1.91 BSC	
LW1	.281	.291	7.14	7.39
LW2	.090	.100	2.29	2.54
Q1	.030		0.762	
Q2	.030		0.762	



NOTES:

- 1 Dimensions are in inches.
- 2 Millimeters are given for general information only.
- 3 Terminal 1 - collector, terminal 2 - base, terminal 3 - emitter

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [Microsemi manufacturer](#):

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [BC546/116](#) [BC557/116](#) [BSW67A](#) [NTE158](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE63](#) [C4460](#)
[2SA1419T-TD-H](#) [2SA1721-O\(TE85L,F\)](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [2SC5488A-TL-H](#) [2SD2150T100R](#) [SP000011176](#) [FMMTA92QTA](#)
[2N2369ADCSM](#) [2SC2412KT146S](#) [2SC5490A-TL-H](#) [2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#)
[US6T6TR](#) [732314D](#) [CMXT3906 TR](#) [CPH3121-TL-E](#) [CPH6021-TL-H](#) [873787E](#) [UMX21NTR](#) [EMT2T2R](#) [MCH6102-TL-E](#) [FP204-TL-E](#)
[NJL0302DG](#) [2N3583](#) [2SA1434-TB-E](#) [2SC3143-4-TB-E](#) [2SD1621S-TD-E](#) [NTE103](#) [30A02MH-TL-E](#) [NSV40301MZ4T1G](#) [NTE101](#) [NTE13](#)
[NTE15](#) [NTE16001](#)